



imecDARE

DAREI80U

UMC L180 MM/RF 1.8V/3.3V, SINGLE POLY 6 METAL (1P6M), PSUB/TWIN-WELL CMOS

STATUS



STATUS

Application chips overview

ADK

Library

IP

Logistics

STATUS

Application chips overview

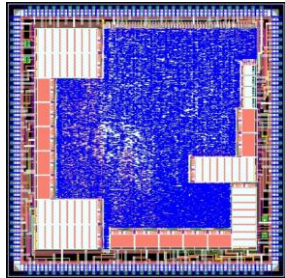
ADK

Library

IP

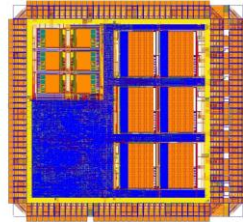
Logistics

APPLICATION CHIPS OVERVIEW I



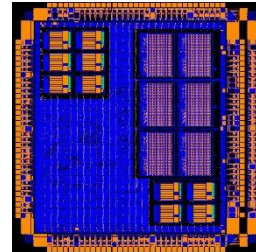
KNUT

*Flight Models
2nd lot qualified*



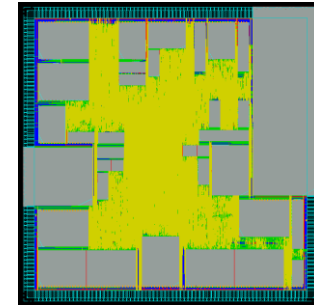
LARS

Characterized



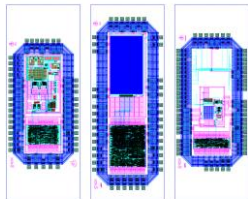
LARS2

Taped out



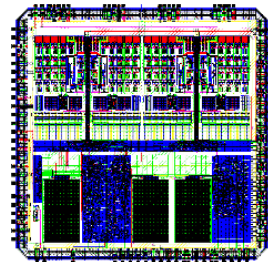
DPC

Under Test



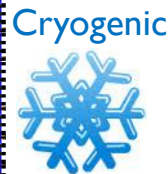
Shamrock

*Radiation
Tested*



FAIR

*Samples
delivered*

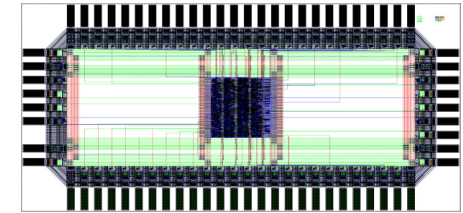
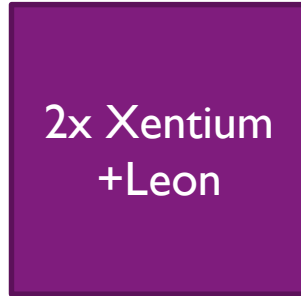
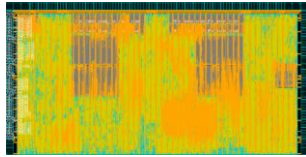


Cryogenic

APPLICATION CHIPS OVERVIEW II



ARQUIMEA



XentiumDARE

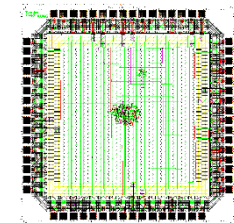
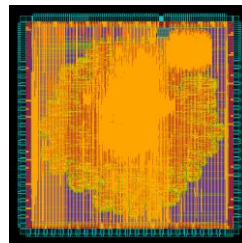
*Tested
(cf. DSP days)*

SSDP

*Architecture
Definition*

Digital companion
to I3T80 chip

*Built into Hybrid &
qualified*



CLP

*Architecture
Defined*

SpVRouter

Tested

uC

*Architecture
Definition*

Relco

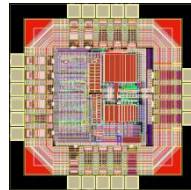
Tested

APPLICATION CHIPS OVERVIEW III



Fast
ADC

Fast ADC
Detailed Design



CAN transceiver
Tested

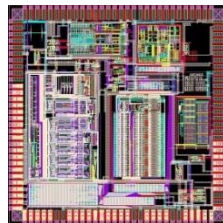


LVDS
Dual
Transceiver

LVDS
4x4 Cross
point
Switch

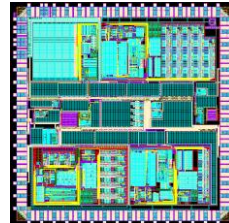
LVDS
*2nd test vehicle
Taped out*

ARQUIMEA



HF configurable
instrumentation
front-end
Tested

ARQUIMEA



MF configurable
instrumentation
front-end
Taped out

STATUS

Application chips overview

ADK

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Logistics

DARE+ project:

- Device Test Vehicle
- Library Test Vehicle
- XentiumDARE Application ASIC

Final Present tomorrow @9AM

STATUS

Application chips overview

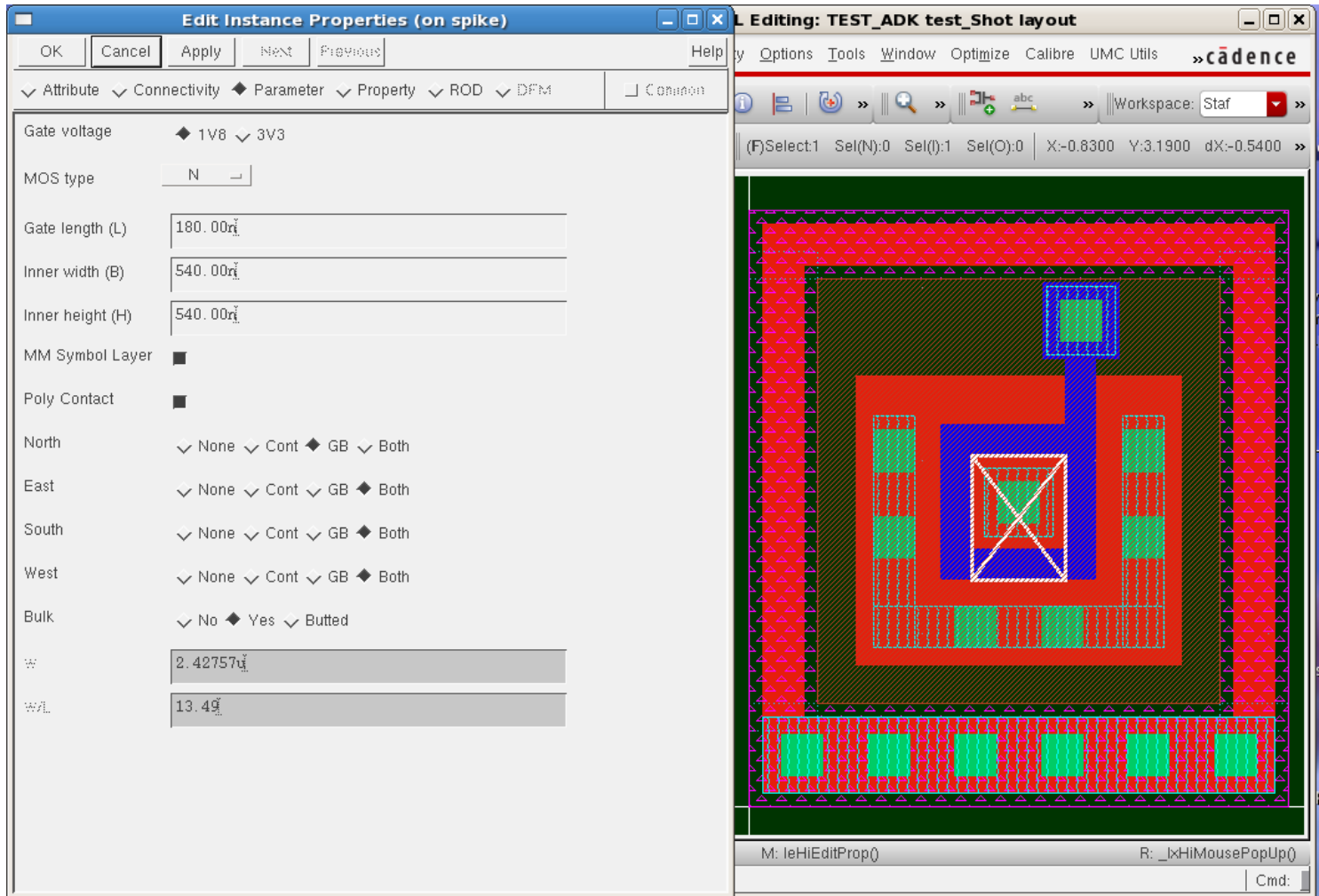
ADK

Library

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Logistics

ADK LAYOUT/SCHEMA PCELL



ADK

LVS AND PARASITIC EXTRACTION

- Recognition of ELT models and W/L computation according to CERN formula
- Check inner-outer diffusion matching between schema and layout
- Improved transistor parasitics modeling in cooperation with  CMOSIS
image sensors

ADK RAD CHECK

Additional check for:

- ▶ Poly crosses P+diffusion guard
- ▶ Nmos gate NOT enclosed
- ▶ 1.8V Leaky STRAIGHT N+diffusion regions
- ▶ 3.3V Leaky STRAIGHT N+diffusion regions
- ▶ 1.8V Leaky ELT N+diffusion regions
- ▶ 3.3V Leaky ELT N+diffusion regions
- ▶ Leaky Nwell-N+diffusion regions
- ▶ Leaky Nwell-Nwell regions

STATUS

Application chips overview

ADK

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LIBRARY

Releases

V3.1	Nov 2007	Orig. LEONDARE, Ocean/SLC, IC4,
V4.1	Oct 2010	IC5, ELC, Encounter
V5.3	Feb 2013	IC6, Altos, Encounter (DARE+ elements)
V5.4	Aug 2013	New & impr. I/O, LVDS characterization, PLL
V5.5	Dec 2013	IBIS models, docs update, EM optimization in I/O

LIBRARY UPDATES

► DAREI80_CORE

- MULLERCRLSH added
- XICGD2, XICGD4 and XICGD9 added
- AOI2ID0, OAI2ID0 and SRMUXI2I added
- *D6 invertors and buffers added
- Input stage *D4 and *D9 buffers updated to D2
- Name update:AOI2I* to AOI22*, OAI2I* to OAI22*
- MEI abutment fix TIEH and TIEL
- Decap cells added
- Guidelines for radiation hardened (front-end) design

LIBRARY UPDATES

► DAREI80_IO

- Bonding pads separated from IO
- 2.5V cells removed
- Diodes removed between 1.8V and 3.3V
- ESD protection to VDD updated
- BREAKER_ALL and FILLER_ESD added
- Schmitt trigger levels adjusted
- SRC versions added
- 8mA and 16mA drive strength added
- 5VT input stage updated
- Nwell strap at VDD removed
- 20KA compatibility

LIBRARY UPDATES

▶ **DAREI80_LVDS**

- No integrated bonding pads
- Extended Common Mode Input Range
- Power down added
- Selectable reference

STATUS

Application chips overview

ADK

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IP

Logistics

IP



All soft IP can be used in
rad-hard aware back-end flow
like LEON3, EDAC, SpW IP, ...

SRAM

Single port compiler

Parameter	Minimum	Typical	Maximum	Unit
Junction Temperature	-55	27	145	°C
Supply Voltage	1.62	1.8	1.98	V
SRAM Size	256	-	262144	bits
Word Count	32	-	8192	words
Word Length	8	-	256	bits
Write Mask Granularity	8	-	-	bits
Operating Frequency	-	-	200	MHz
SRAM Cell Cross-section	NA	33×10^{-9}	NA	cm ²

Dual port compiler

Parameter	Minimum	Typical	Maximum	Unit
Junction Temperature	-55	27	145	°C
Supply Voltage	1.62	1.8	1.98	V
SRAM Size	256	-	262144	Bits
Word Count	32	-	8192	Words
Word Length	8	-	256	Bits
Write Mask Granularity	8	-	-	bits
Operating Frequency	-	-	TBD	MHz
SRAM Cell Cross-section	NA	120×10^{-9}	NA	cm ²

SRAM

Single port compiler

Parameter	Minimum	Typical	Maximum	Unit
Junction Temperature	-55	27	145	°C
Supply Voltage	1.62	1.8	1.98	V
SRAM Size	256	-	262144	bits
Word Count	32	-	8192	words
Word Length	8	-	256	bits
Write Mask Granularity	8	-	-	bits
Operating Frequency	-	-	TBD	MHz
SRAM Cell Cross-section	NA	120x10 ⁻⁹	NA	cm ²

After .lib/.db generation, each new instance will be verified through PVT corners.

Silicon Proven

STATUS

Application chips overview

ADK

Library

IP

Logistics

LOGISITCS

- MTC-Online will disappear
- Data space per project or company for distribution of kits and other files.
- dare_support@imec.be is preferred way for DARE related support



imecDARE

